EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	11	transistor and memory and (oxide same silicon) and (mos "metal oxide semiconductor") and (fet "field effect transistor") and (write adj word$1line) and bit$1line and (read adj word$1line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 12:00
S2	34	transistor and memory and (fet "field effect transistor") and (write adj word$1line) and bit$1line and (read adj word$1line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 11:14
S5	129	diode and transistor and capacitor and memory and word$1line and bit$1line and (gate near5 (source drain)) and (mos "metal oxied semiconductor") and (fet "field effect transistor")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 11:26
S6	20	(US-20040120200-$ or US-20040132250-$).did. or (US-4370737-$ or US-4954854-$ or US-5278785-$ or US-5299154-$ or US-5307315-$ or US-5397946-$ or US-5822246-$ or US-5841703-$ or US-5910924-$ or US-6134146-$ or US-6160440-$ or US-6212107-$ or US-6359947-$ or US-6515903-$ or US-6768156-$ or US-6950341-$ or US-6980448-$ or US-7027326-$).did.	US-PGPUB; USPAT	OR	ON	2006/06/20 11:41
S7	20	(US-20040120200-$ or US-20040132250-$).did. or (US-4370737-$ or US-4954854-$ or US-5278785-$ or US-5299154-$ or US-5307315-$ or US-5397946-$ or US-5822246-$ or US-5841703-$ or US-5910924-$ or US-6134146-$ or US-6160440-$ or US-6212107-$ or US-6359947-$ or US-6515903-$ or US-6768156-$ or US-6950341-$ or US-6980448-$ or US-7027326-$).did.	US-PGPUB; USPAT	OR	ON	2006/06/20 13:59
S8	16	S7 and (trench well groove) and (mos (metal adj oxide adj semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:04

EAST Search History

S9	20	S7 and word$1line and bit$1line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 14:01
S10	2	("20050128803").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 15:58
S11	19442	"storage cell"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:05
S12	2457	"storage cell" with transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:05
S13	1335	"storage cell" with transistor same (source drain terminal gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:06
S14	7	"storage cell" with transistor same (source drain terminal gate) and 257/288.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:10
S15	6824	(dram dynamic adj random adj access adj memory dynamic adj ram) and (two three "2" "3") adj (t transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:14
S16	83	(dram dynamic adj random adj access adj memory dynamic adj ram) and (two three "2" "3") adj (t transistor) and silicon and oxide and cylindrical and planar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/02 14:23

S17	171	plan$4 same gate and dram and transistor same capacitor same diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 08:25
S18	93	"poly trench"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 08:31
S19	9	"poly trench" and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 08:35
S20	2	("6916745").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/03 09:10
S21	2884	diode and transistor and capacitor and trench and silicon and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 09:11
S22	422	diode and transistor and capacitor and trench same gate same silicon same oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 09:12
S23	41	diode and transistor and capacitor and trench same gate same silicon same oxide and cylindrical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/03 09:17
S24	2	("4649625").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/03 10:55

S25	518	(365/175).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/03 10:55
S26	1639	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/03 12:00
S27	528	(365/175).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 15:59
S28	1785	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 15:59
S29	157	(S27 S28) and @pd>"20061003"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 15:59
S30	18	(S27 S28) and @pd>"20061003" and @ad<"20031211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:00
S31	5	(S27 S28) and @pd>"20061003" and @ad<"20031211" and diode and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:02

S32	8572	transistor and diode and (word$1line word adj line)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:03
S33	4702	transistor and diode and capacitor and (word$1line word adj line)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:04
S34	3653	transistor and diode and capacitor and (word$1line word adj line) and @ad<"20031211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:05
S35	3542	transistor and diode and capacitor and (word$1line word adj line) and memory and @ad<"20031211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:06
S36	92	transistor and diode and capacitor and (word$1line word adj line) and memory and (shallow near3 trench sti) same gate and @ad<"20031211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 16:07